

TO-92 Plastic-Encapsulate Transistors

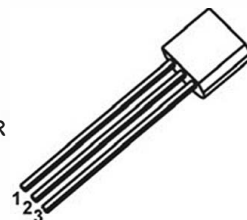
A733 TRANSISTOR (PNP)

FEATURE

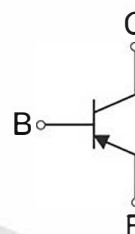
- Power dissipation

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Power Dissipation	250	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Junction and Storage Temperature	-55~+150	$^{\circ}\text{C}$

$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	90	200	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-0.18	-0.3	V
Base-emitter voltage	V_{BE}	$V_{CE} = -6\text{V}, I_C = -1.0\text{mA}$	-0.58	-0.62	-0.68	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -10\text{mA}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			6	pF
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.3\text{mA},$ $R_g = 10\text{k}\Omega, f = 100\text{Hz}$			20	dB

CLASSIFICATION OF h_{FE}

Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600